

IN THE CLAIMS

Please amend claims 5, 6, 8, and 9 as follows:

5 (Amended). A method for forming an interface between a silicon surface and a dielectric layer comprising:

C¹

providing a silicon substrate with an upper surface;

forming an amorphous region in said upper surface by exposing said upper surface to halogen species;

forming a capping layer on said amorphous region; and

forming a dielectric layer on said capping layer.

C²

6 (Twice amended). The method of claim 5 further comprising removing a dielectric layer from said upper surface prior to forming said amorphous region.

7 (Amended). The method of claim 5 wherein said halogen species is selected from the group consisting of chlorine, bromine, iodine and fluorine.

C³

8 (Amended). The method of claim 5 wherein said forming said amorphous further comprises:

exposing a chlorine containing gas to UV radiation to form excited chlorine species;

heating said upper surface to a temperature between 50°C and 250°C; and

exposing said heated upper surface to said excited chlorine species.

C3
Circled.

9 (Amended). The method of claim 5 wherein said dielectric layer is formed using a material selected from the group consisting of silicon oxide, silicon nitride, silicon oxynitride, and a silicate.
